

# Visualizing Oxide Breakdown and Pit Initiation in Aluminum using *ex situ* Electron Microscopy

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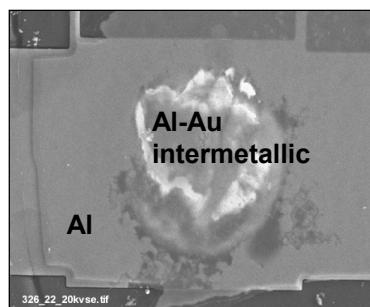
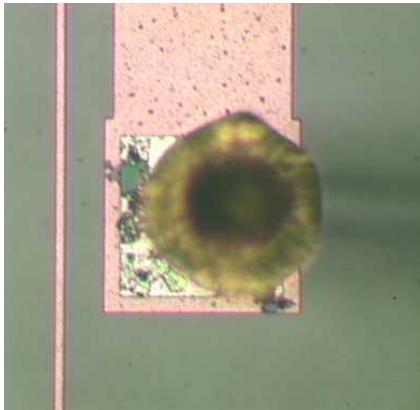
Acknowledgements: P.G. Kotula – TEM, R. Grant - SEM

DOE Basic Energy Sciences Office of Materials & Engineering Sciences

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# Why study pit initiation in aluminum?

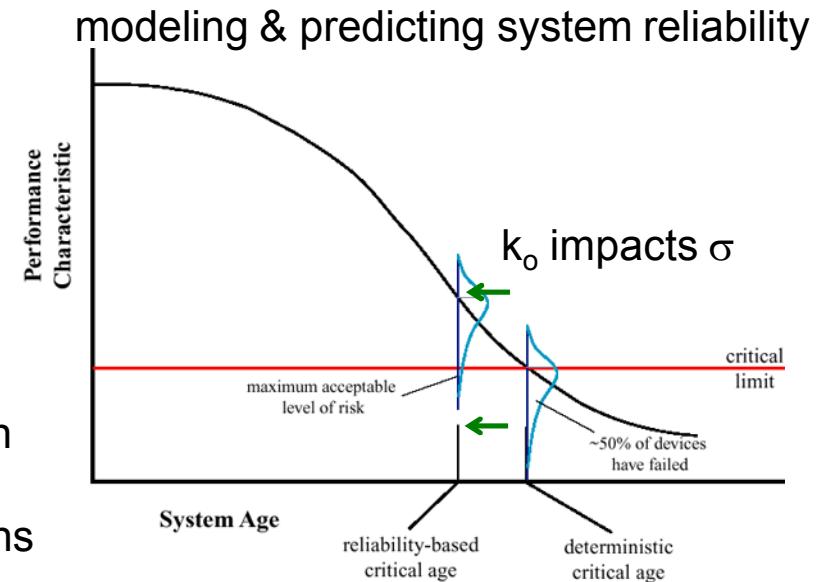
High consequence systems: minimal separation between initiation and damage  
microelectronics – nanomaterials integration & devices



Al interconnects can undergo galvanic corrosion

rate constant ( $k_o$ ) - lump sum term for unknowns

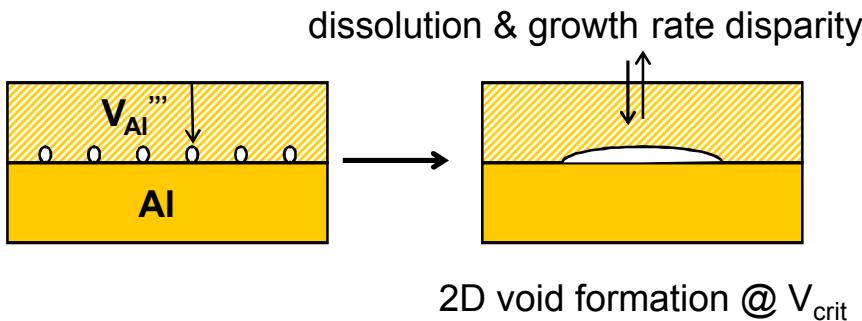
$$\frac{d(\Delta R / R_o)}{dt} = I(\text{defects}) k_o P_{Cl_2}(t) \left\{ 1 - \exp \left[ - \left( \frac{H(t)}{\eta} \right)^\beta \right] \right\} \exp \left[ - \frac{E_a}{RT(t)} \right]$$



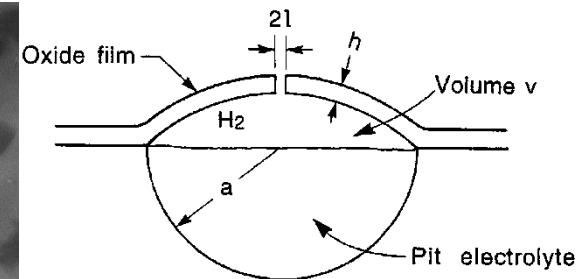
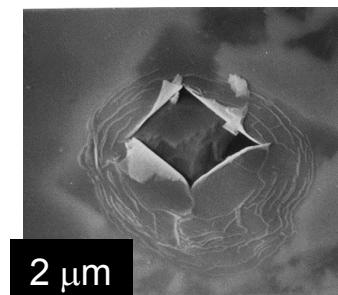
Reliability prediction requires relevant physical & chemical inputs of localized corrosion mechanisms

# Proposed mechanisms for pit initiation

Vacancy condensation - Point Defect Model (Macdonald)

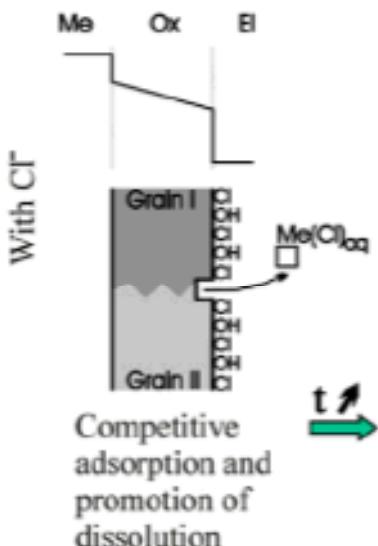


Nano-corrosion cells - Electrokinetic Model (McCafferty)

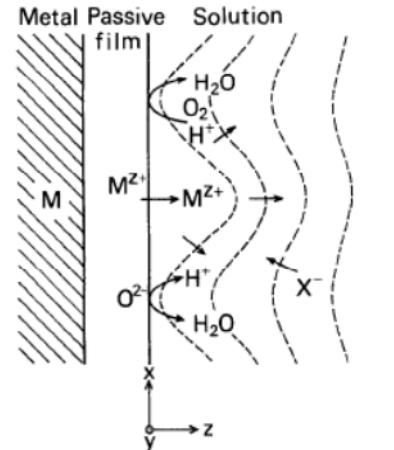


McCafferty & Natishan, 218<sup>th</sup> ECS #1322

Oxide grain boundaries - Marcus, Maurice & Strehbow



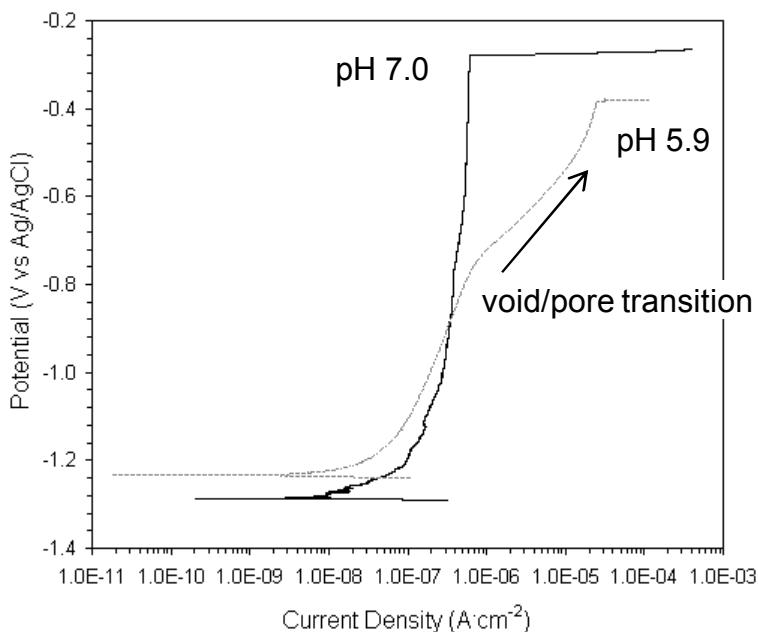
Aggressive anion and electric field perturbation - Okada



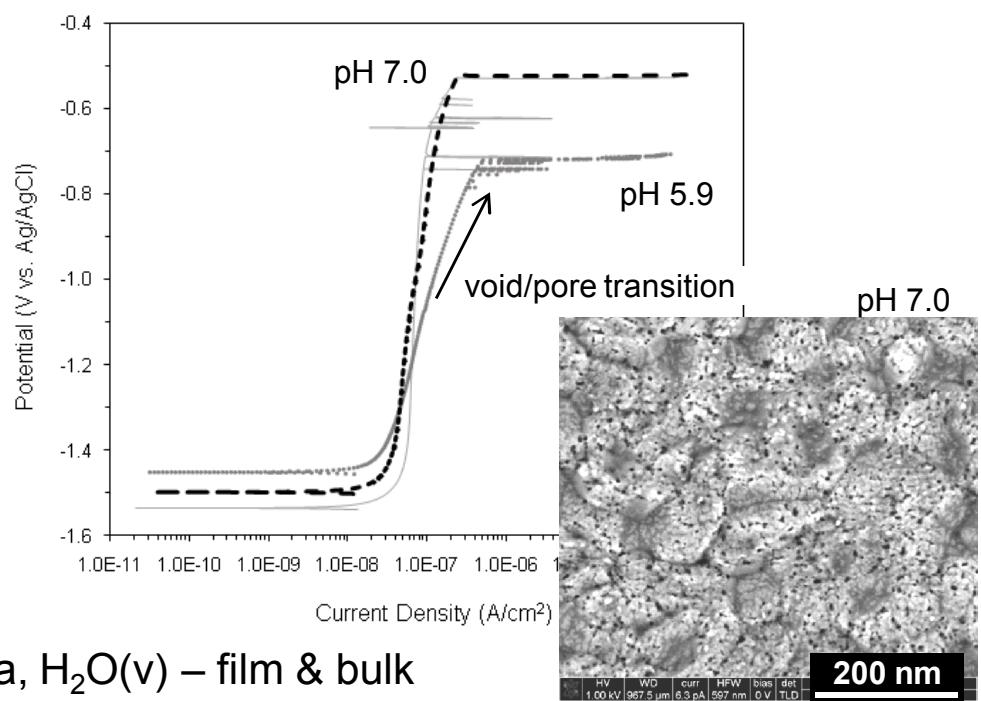
# Pit initiation in an anhydrous oxide on Al coincides with oxide defect activity

~150 nm diameter grain Al(111) film in de-aerated 50 mM NaCl

Macroscale measurements at  $1 \text{ cm}^2$



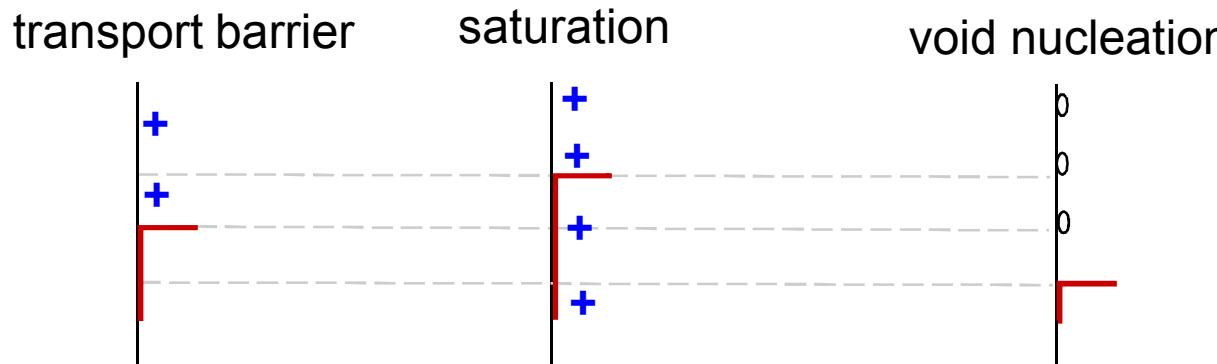
Mesoscale capillary measurements at  $< 0.01 \text{ cm}^2$



Initially anhydrous oxides –  $\text{O}_2$ , O plasma,  $\text{H}_2\text{O}(\text{v})$  – film & bulk including single crystal

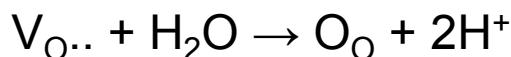
I/V response shows the presence of a proton-activated process that leads to accentuated current generation – anodic dissolution can compete with pit initiation

# Void nucleation results from defect response to applied field

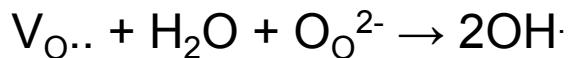


\*interfacial  $V_{O..}^i$ .. Al oxidation increases  $V_{O..}$  barrier relieved

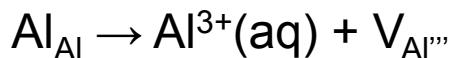
$V_{O..}$  saturation through a simple equilibrium:



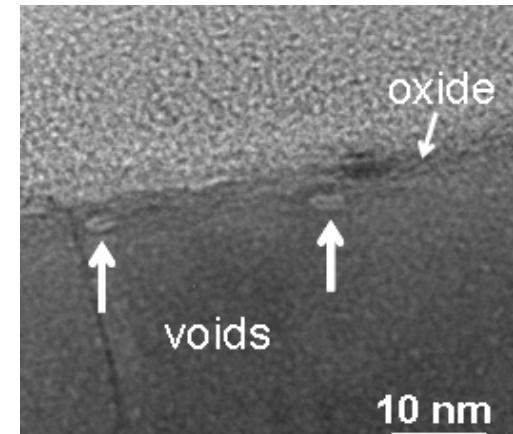
Alternate reaction to consider:



Ox:El interface barriers:



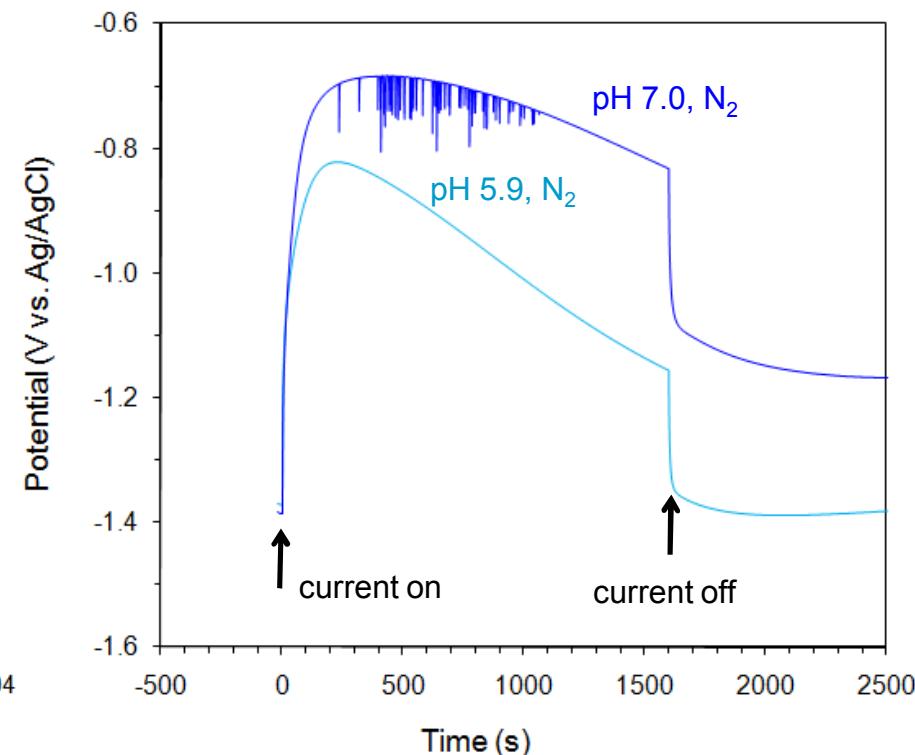
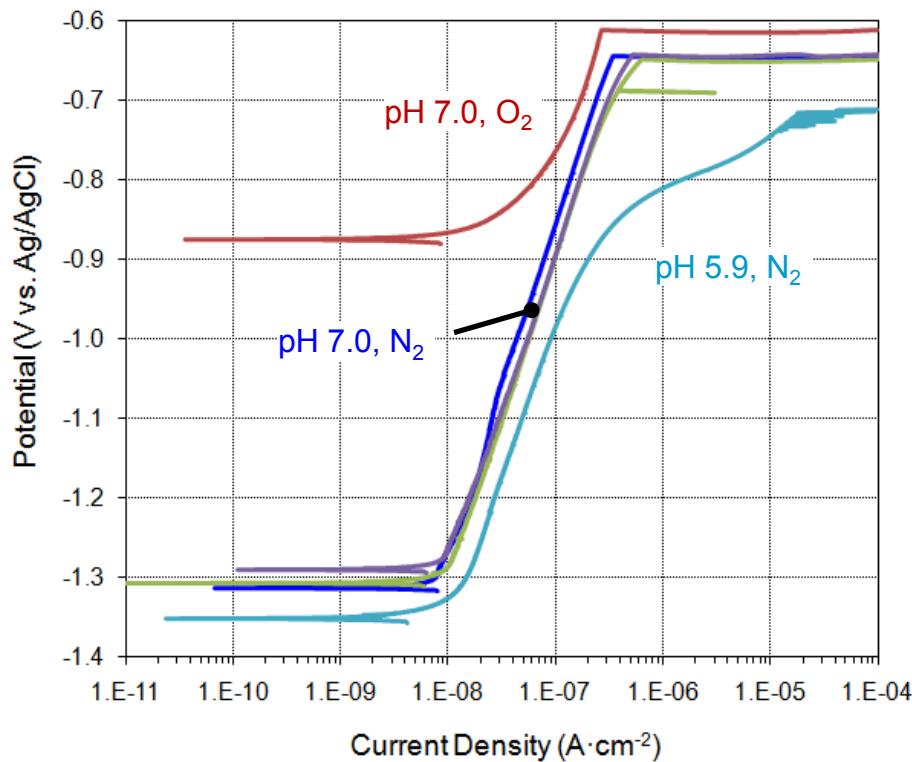
retarded by surface adsorbates or chelating species



Can voids contribute to pit initiation?

# Chronopotentiometry highlights the co-incidence of pitting & defect activity

700 nm thick Al(111) film in de-aerated 50 mM NaCl

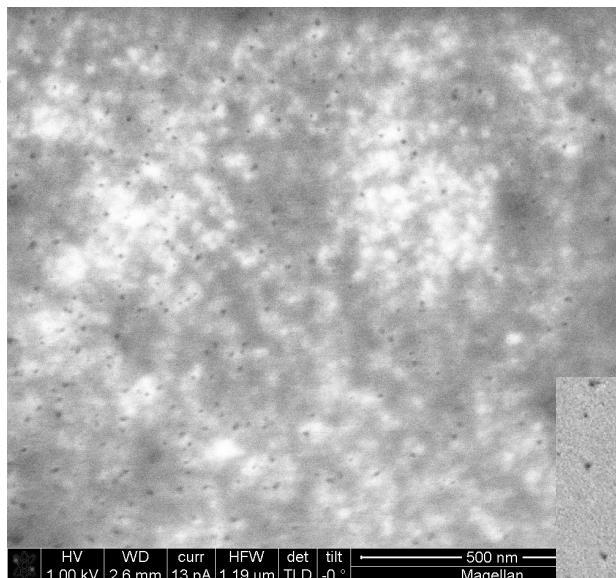
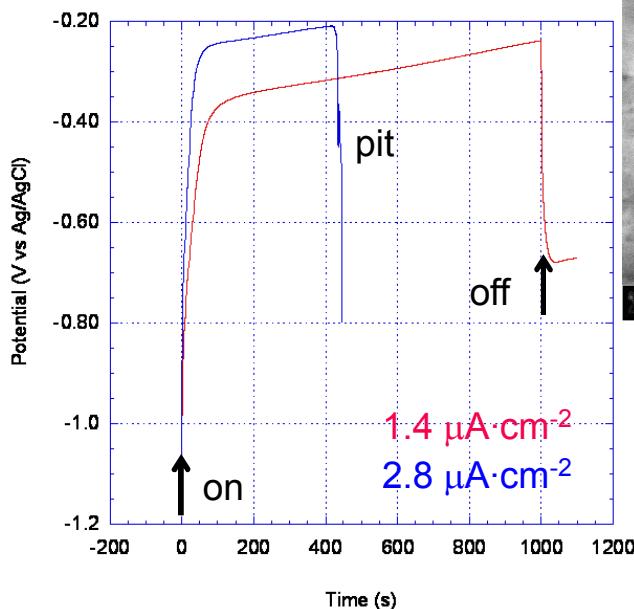


Pitting and accentuated dissolution compete

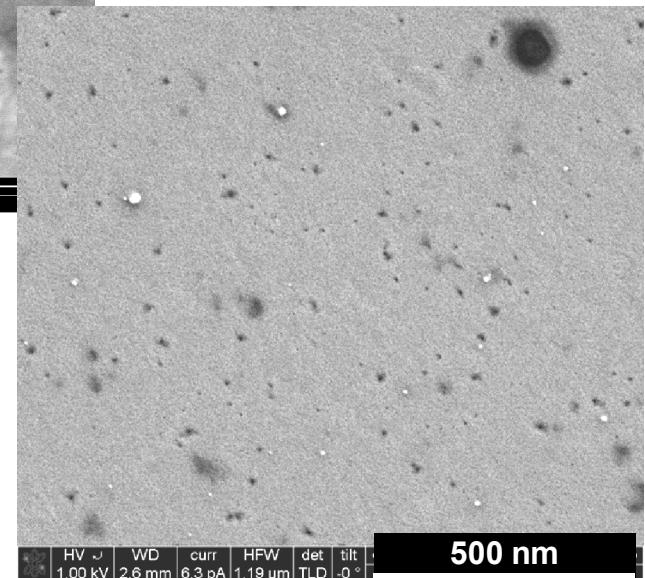
# Similar defect processes operative in *not so model* oxides

99.999% polycrystalline Al aqueous alumina (30 nm polish) – oxide allowed to dry

equilibrated 1 hour 50 mM Cl<sup>-</sup>

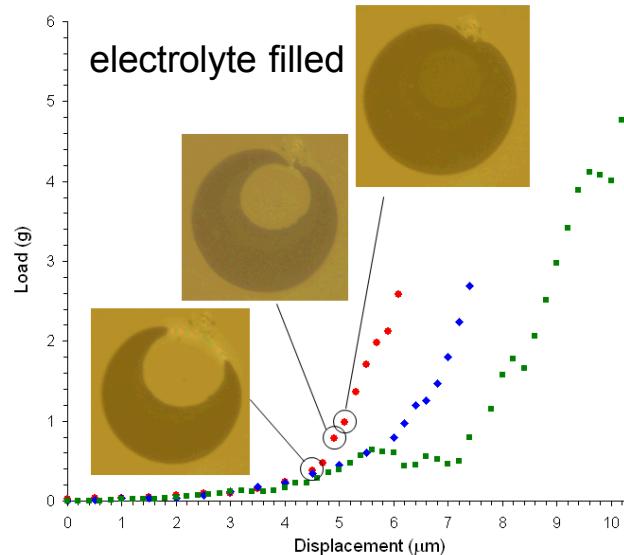
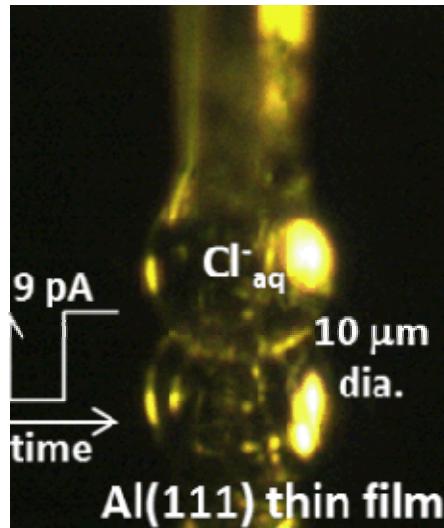
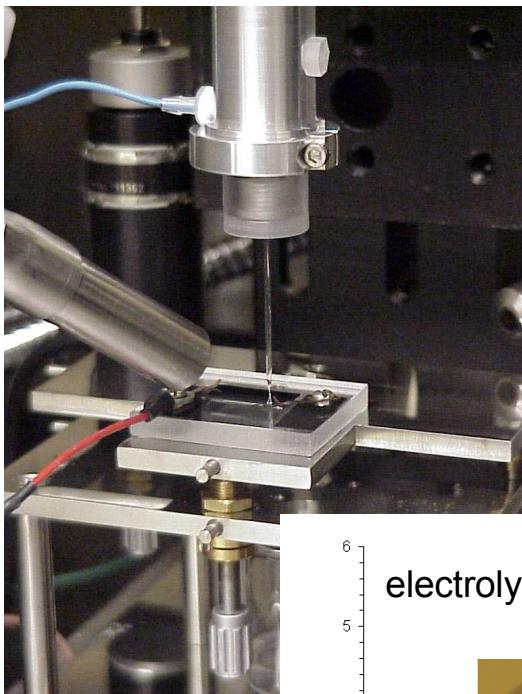


1.4  $\mu\text{A}\cdot\text{cm}^{-2}$ , 1.4 mC

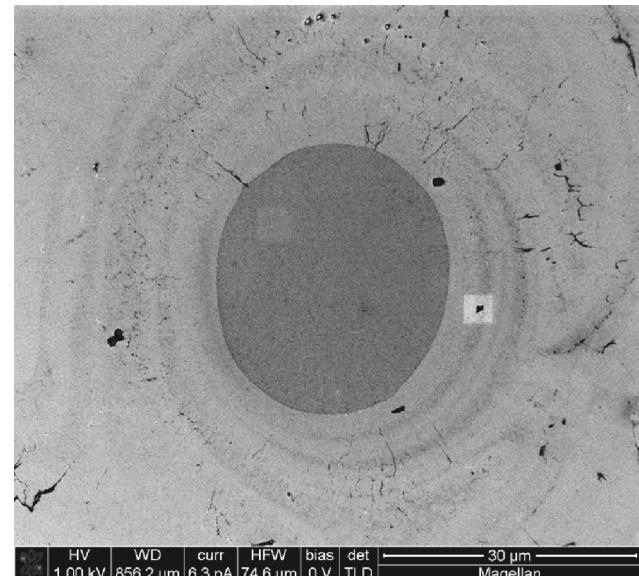


Model oxides may represent one way of probing the limiting cases of defect chemistry

# Can more detail be learned by restricting area to enable imaging?



Snapshot approach

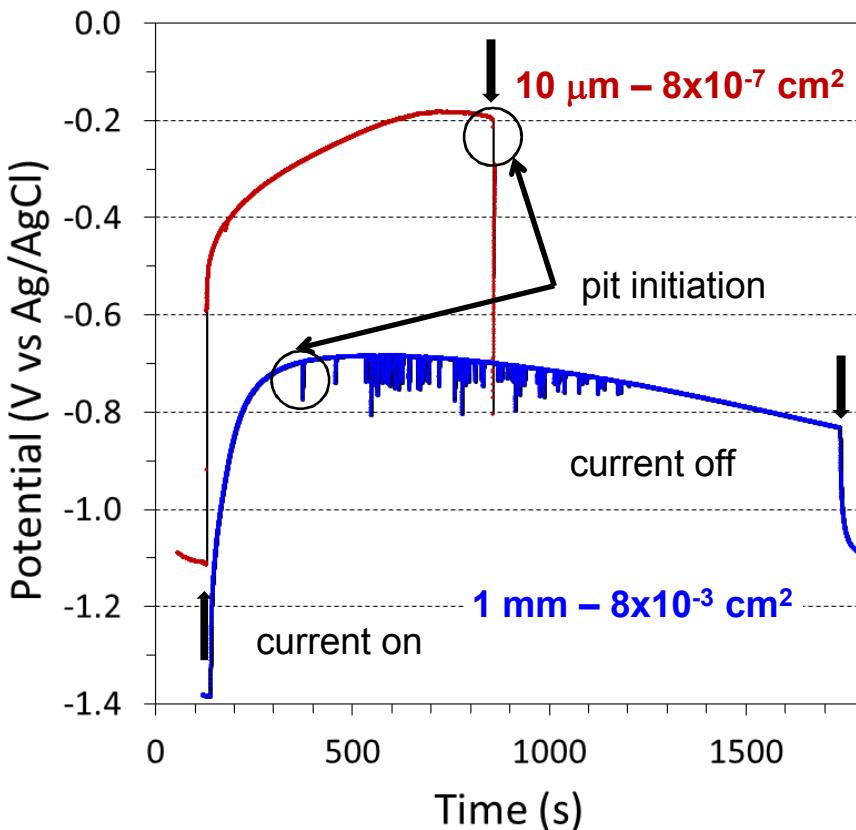


Size limits – leak free seals with minimal under seal activity at 5 - 20  $\mu\text{m}$  diameter,  $1 \times 10^{-7}$  -  $1 \times 10^{-6}$   $\text{cm}^2$

Current limits – galvanostatic polarization at relevant current densities

# Microcell Measurements Yield Meaningful Data

Potential response to a current stimulus is consistent across  $1 \text{ cm}^2$  to  $2 \times 10^{-7} \text{ cm}^2$



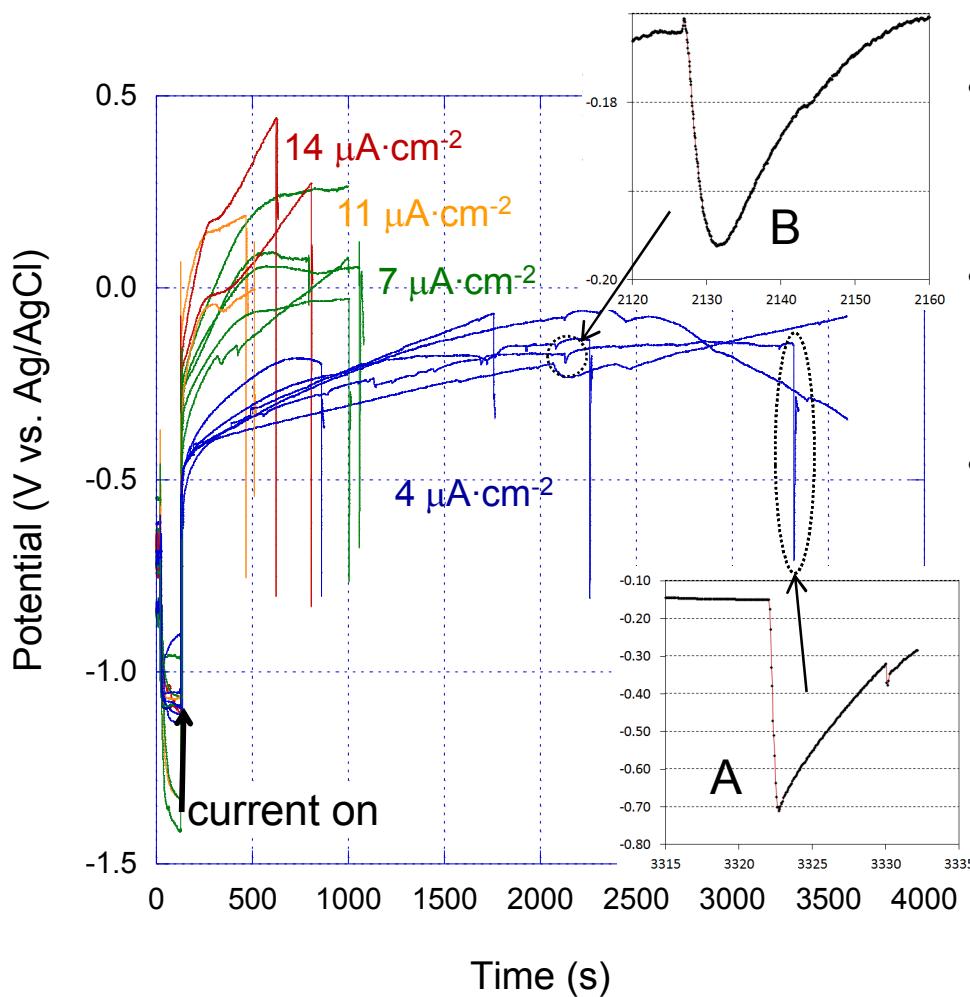
Single events are isolated with small areas

Reduced current – limited available to accelerate pit growth



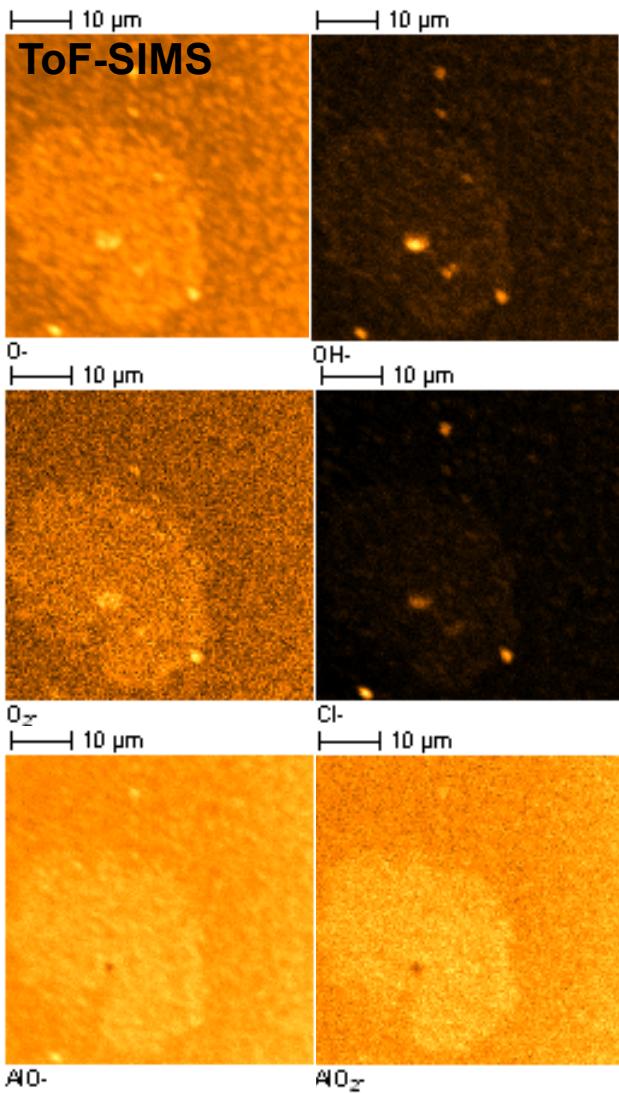
Possible opportunity to characterize initiation sites

# Attributes of Single Discharge Event Experiments

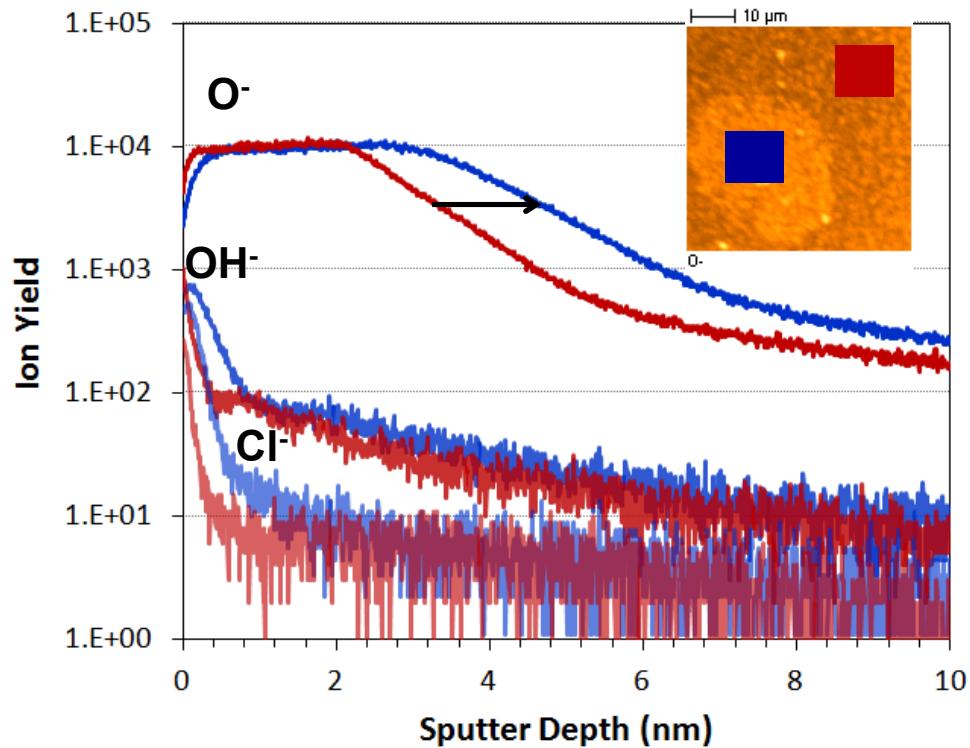


- Increased applied current density – higher probability of creating an event
- increased applied current density - shorter induction time for event occurrence
- Two types of depolarization signatures
  - large magnitude discharge events (A)
  - small magnitude or extended time perturbations (B)

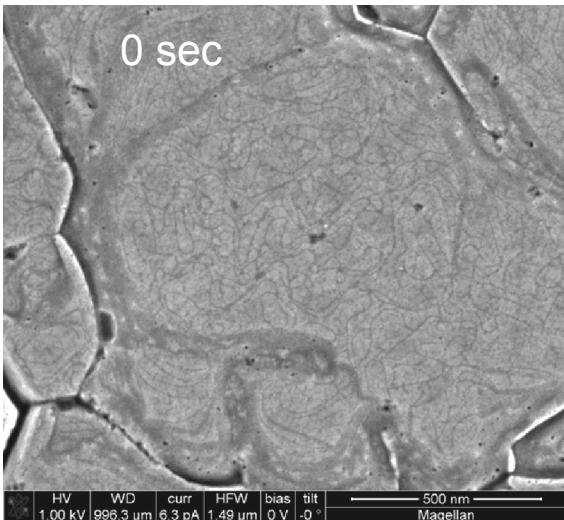
# Polarization drives oxide growth with minimal compositional change to the film



- Oxide growth: 10% from electrolyte immersion, 20 to 40% with polarization
- $\text{Cl}^-$  primarily restricted to the hydrated outer layer



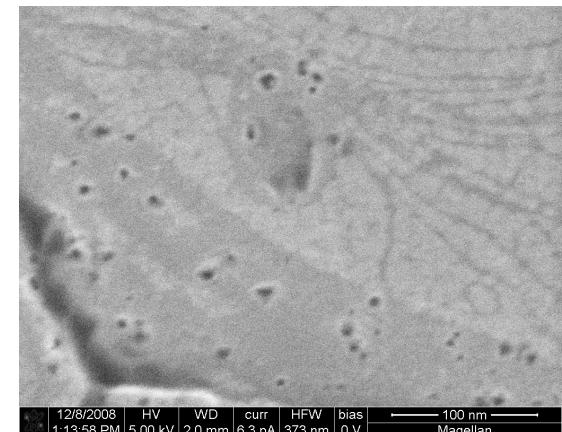
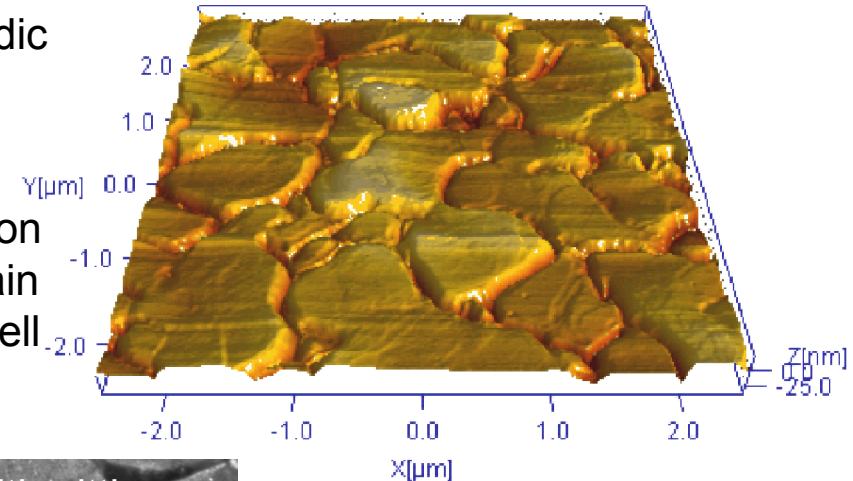
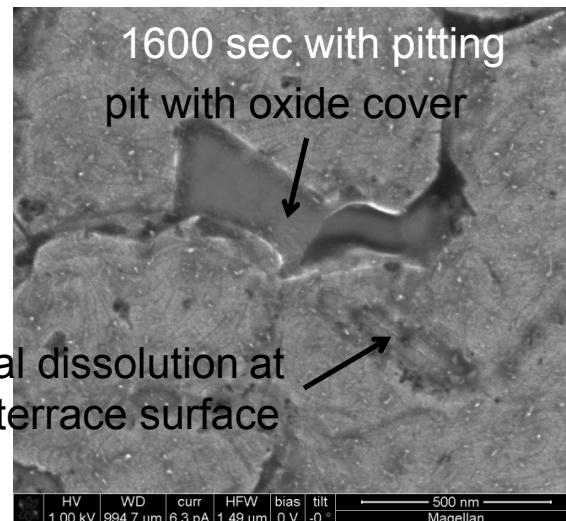
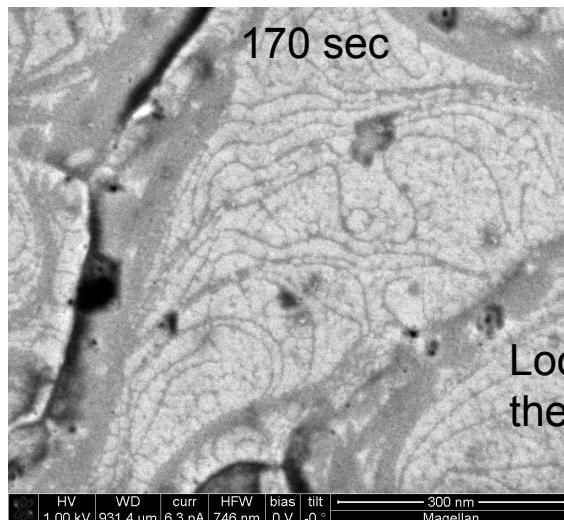
# Structural impact of polarization is greatest at the high step density facets of the grains



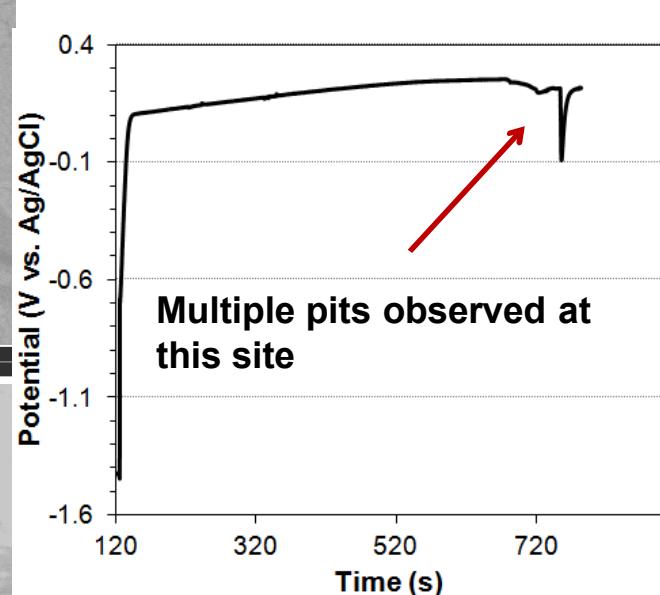
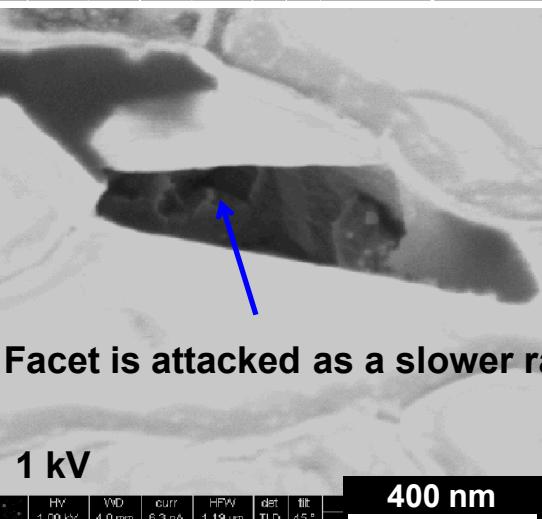
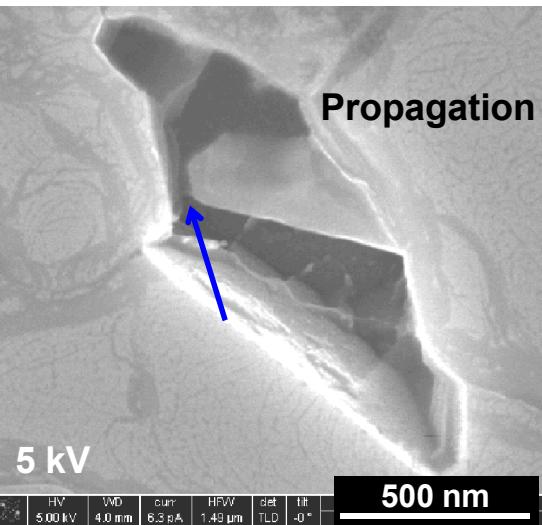
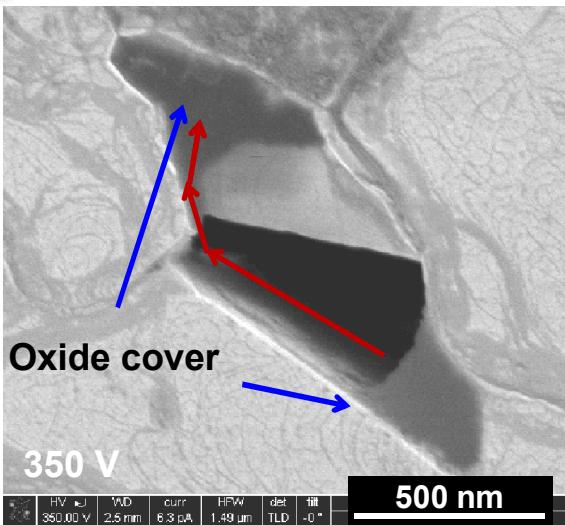
700 nm thick Al(111) film in de-aerated 50 mM NaCl pH 7  
– larger grains for better spatial discrimination

**0.6  $\mu\text{A}\cdot\text{cm}^{-2}$**  anodic polarization for variable time

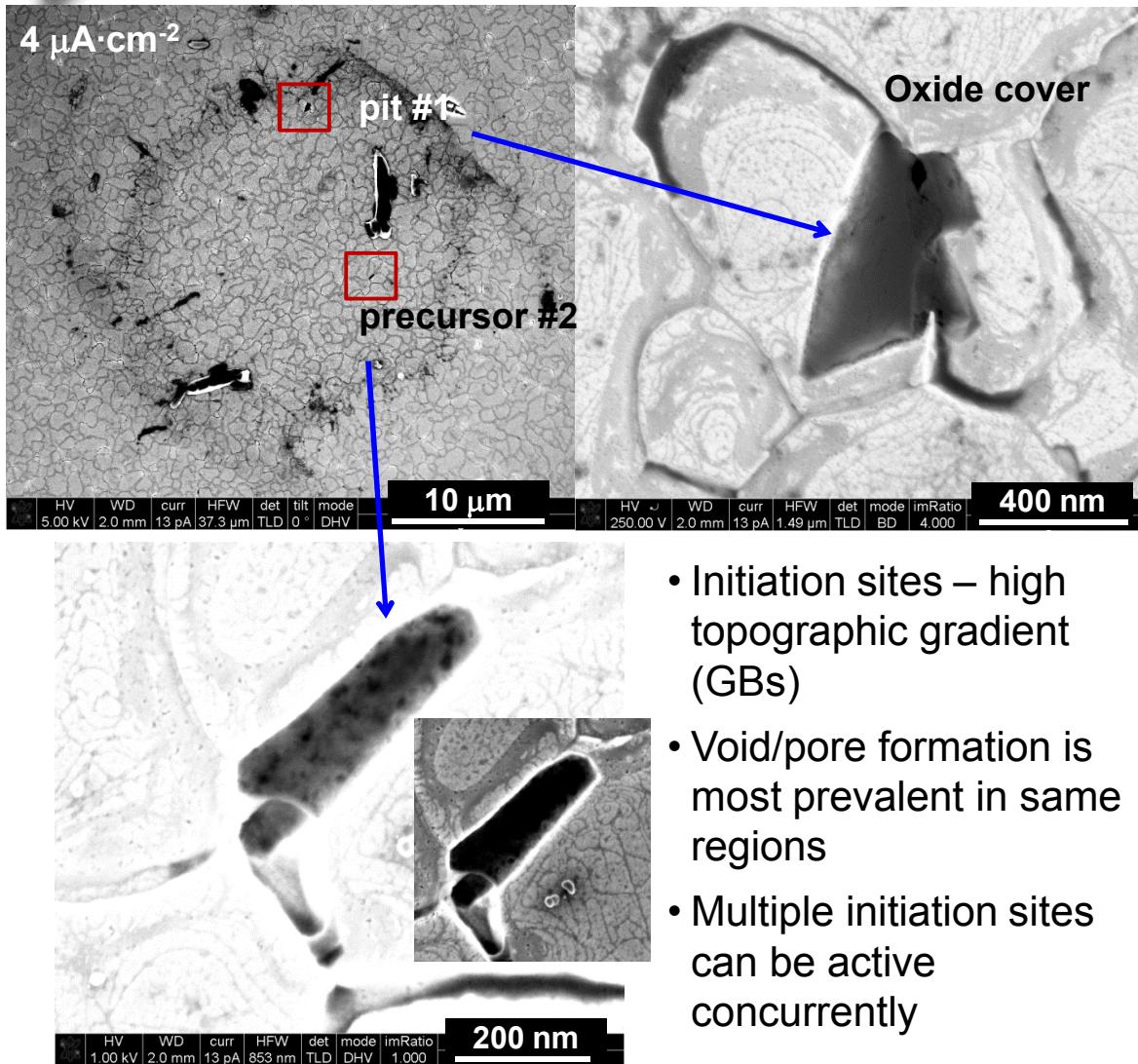
void/pores form on contours into grain boundaries as well as terraces



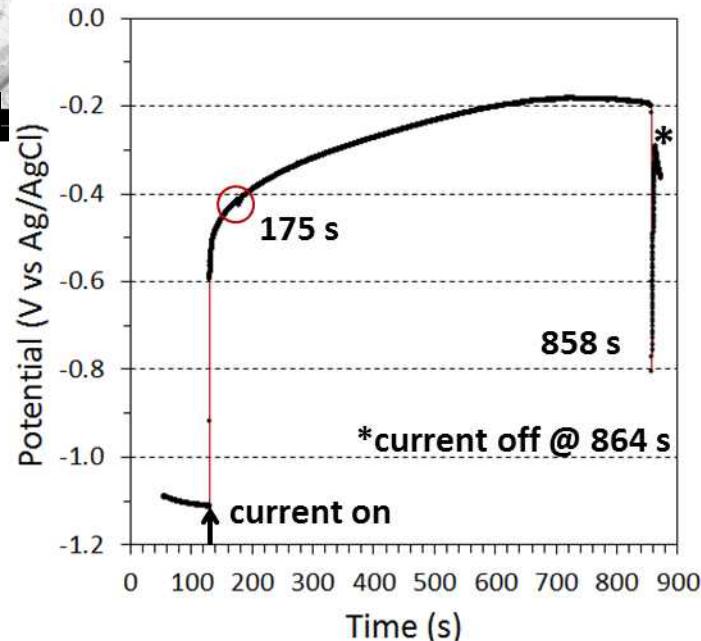
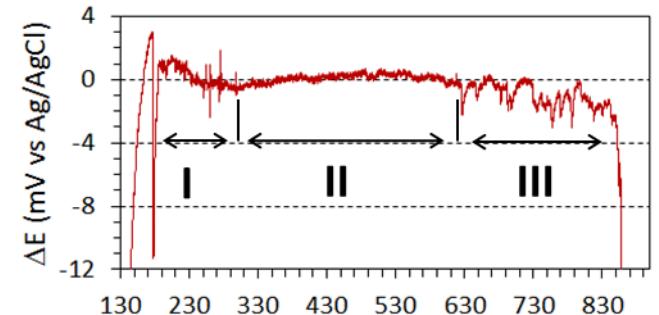
# Evolved pits possess compliant oxide covers



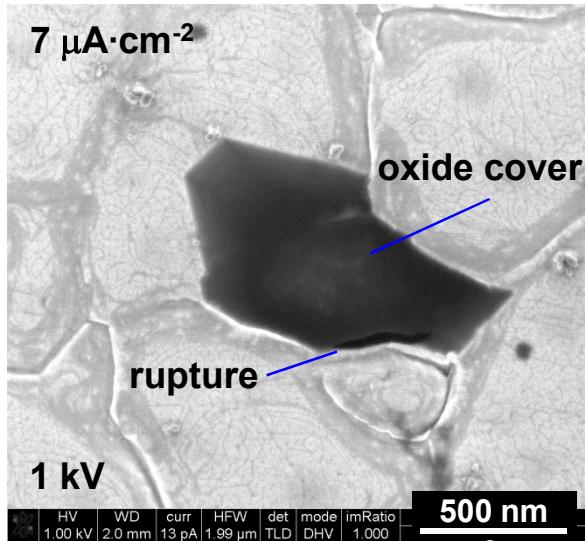
# Sufficient current becomes localized to drive early stage pit formation



Initiation -  $\delta E/\delta t$  fluctuations

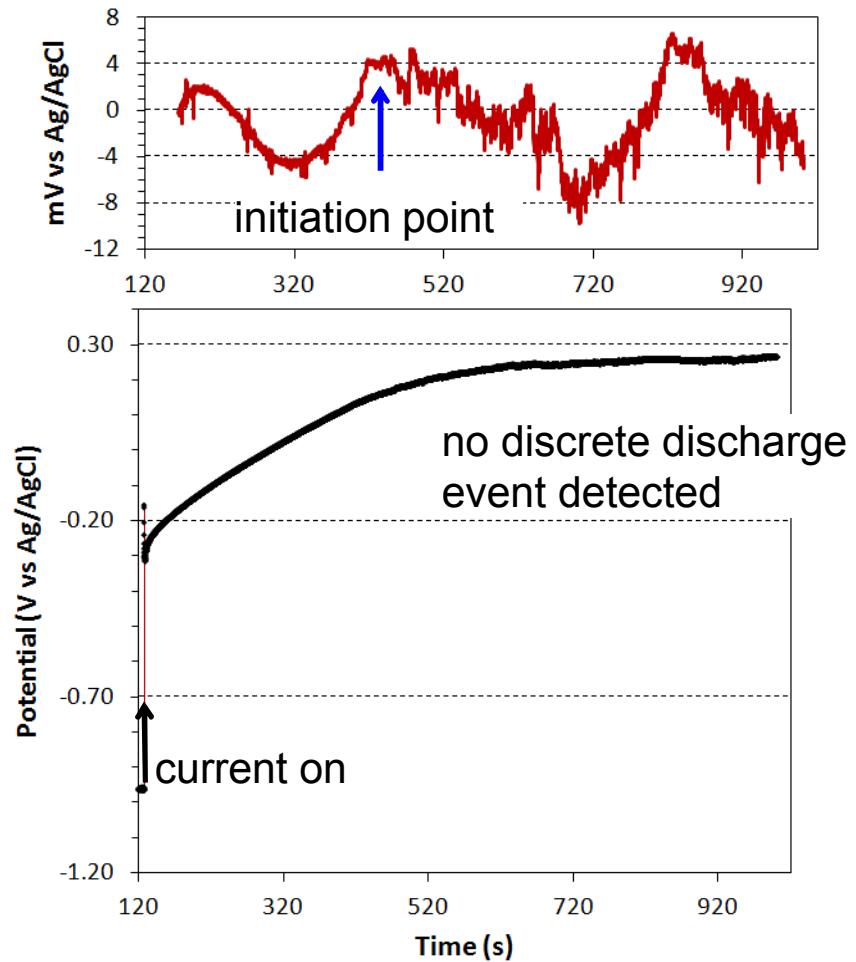


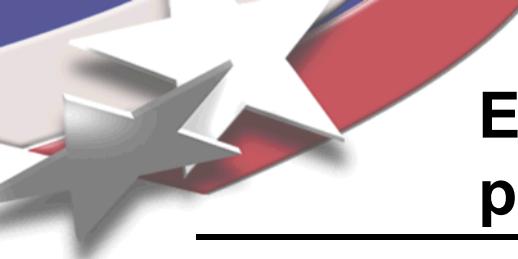
# Electrochemical noise may also signal slow growth of an early stage pit



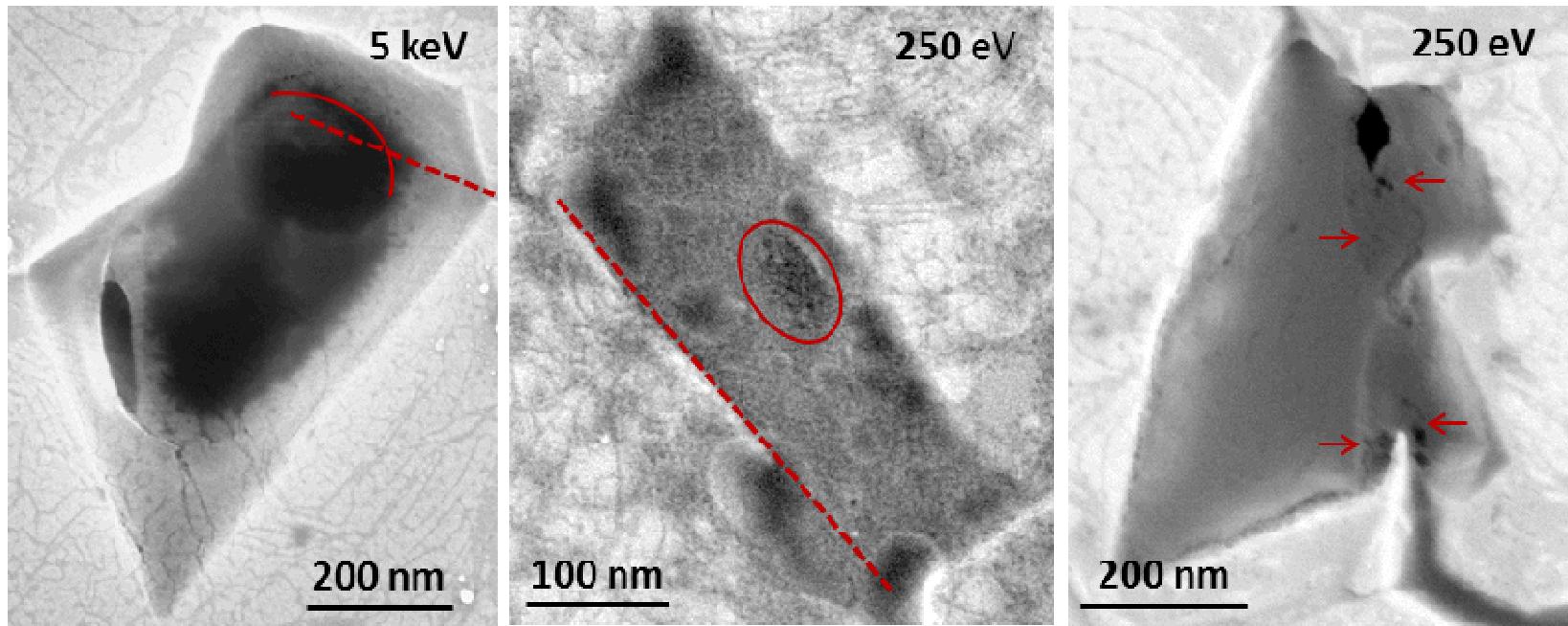
An occluded pit is observed despite the absence of a significant magnitude discharge event

- EC noise is a better indicator of micro-cell activity





# Early stage pits: oxide membranes possess pore clusters

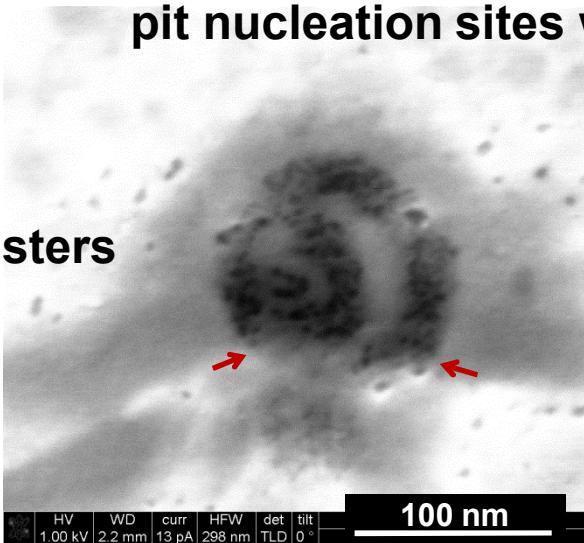


pore clusters appear near grain boundaries

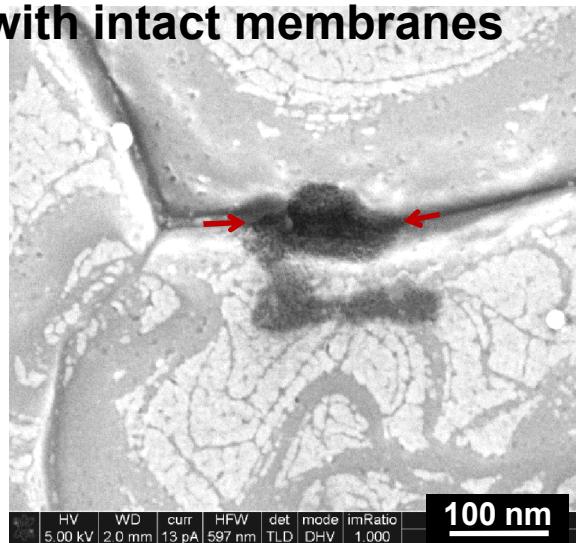
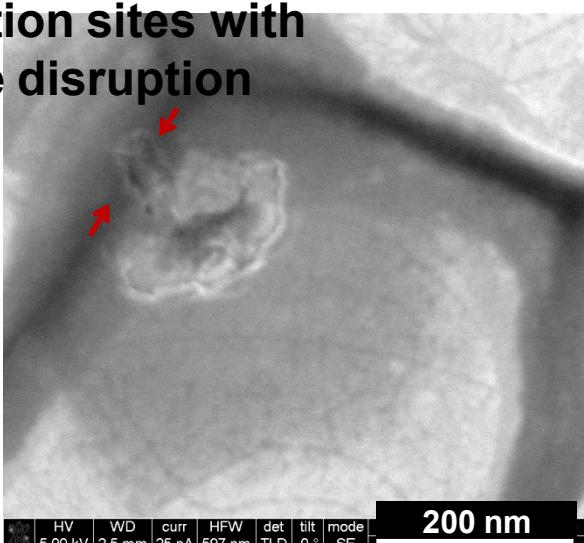
# Pit precursors: concentrated pore clusters are common for high gradient regions

pit nucleation sites with intact membranes

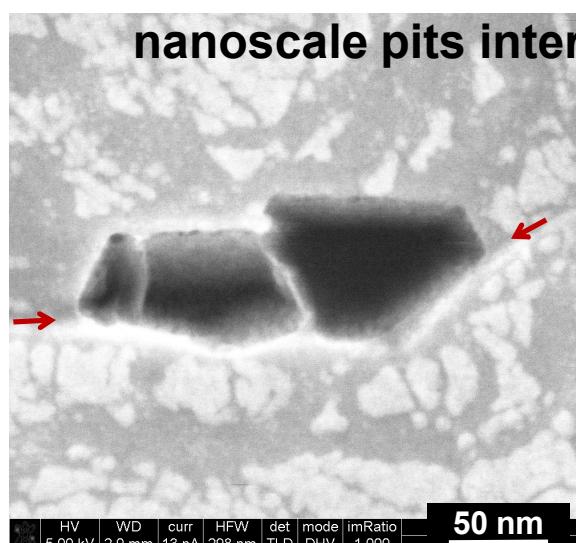
pore clusters



pit nucleation sites with membrane disruption

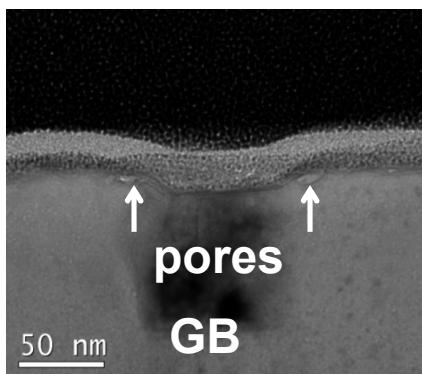
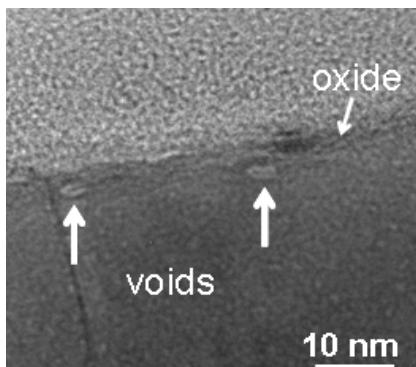


nanoscale pits internal to a grain



# Interfacial Voids as Pit Precursors

Precursor sites  
preferentially at emergent  
facets



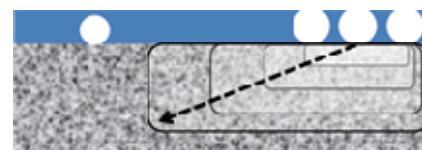
Void nucleation



Void growth and pore formation



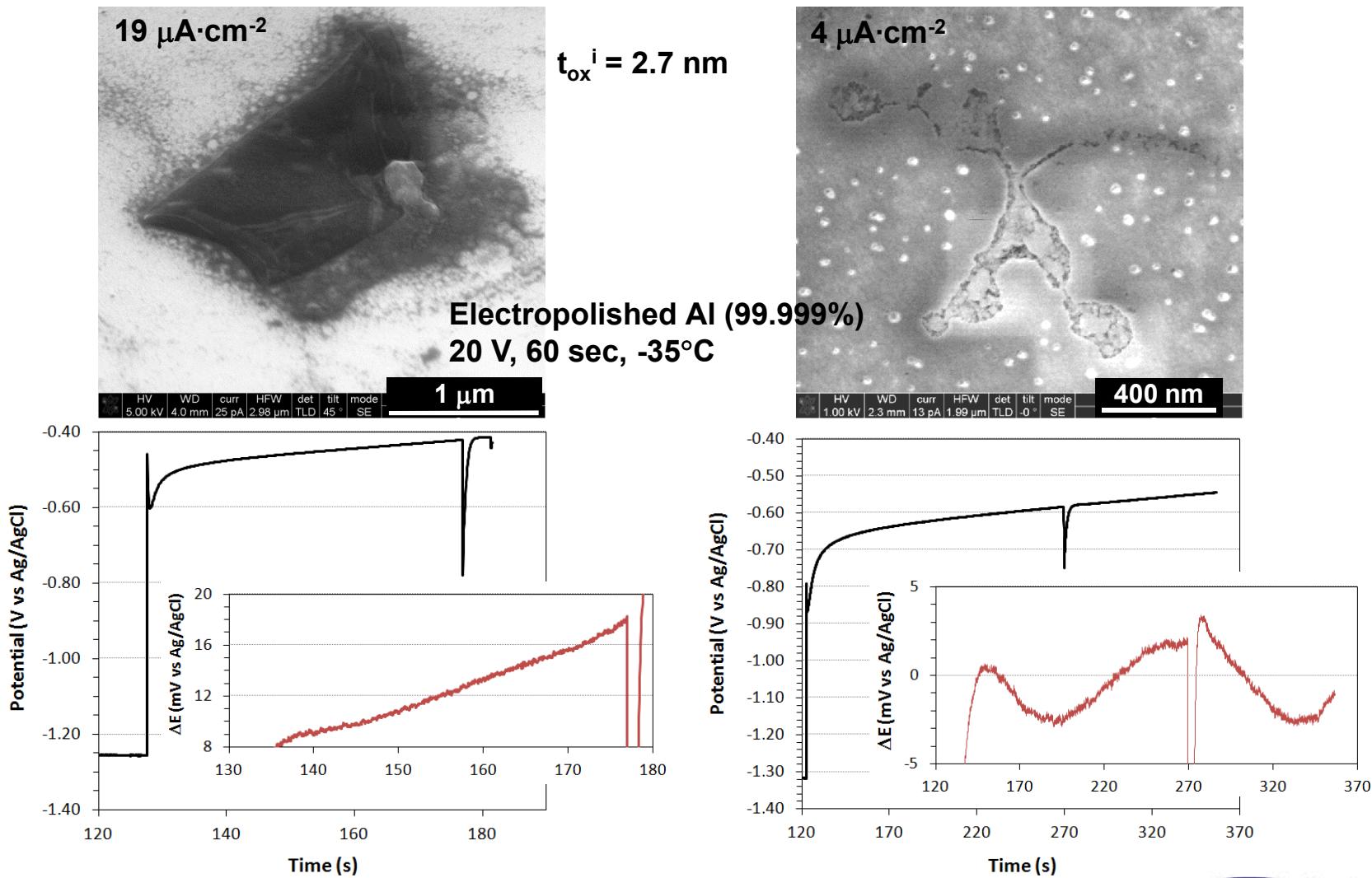
Staple cluster formation – oxide perforation



Pit nucleation under oxide membrane

- O vacancy saturation and interfacial stress produces voids
- higher step densities – lower ionization barrier for Al  $\Rightarrow$  emergent facets more active
- steps serve to lower void nucleation barrier
- voids grow into pores
- initiation occurs – stress due to local topology – destabilizes the pore cluster toward passivation

# Hydrous oxides yield similar responses

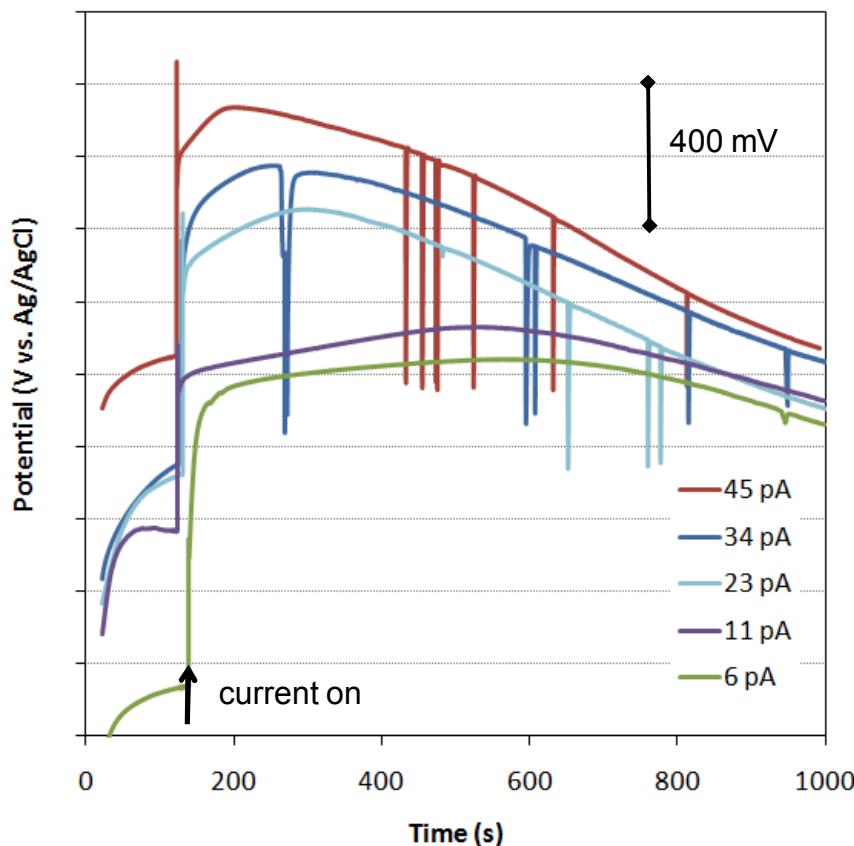




## Back-up Slides

# Defect and breakdown signatures are measureable in the micro-cell

Anodic polarization using a 20  $\mu\text{m}$  diameter capillary



i (pA)	j ( $\mu\text{A}\cdot\text{cm}^{-2}$ )	t <sub>max</sub> (s)	E <sub>max</sub> <sup>*</sup> (mV)	events
45	15	73	45	multiple, frequent
34	11	125	-38	multiple, frequent
23	7	320	-82	multiple, infrequent
11	4	480	-172	multiple, infrequent
6	2	450	-159	single, rarely
3	1	1930	-252	none detected

\*vs. Ag/AgCl

Defect response is observed with anodic polarization

Breakdown events are observed at potentials  $> -550$  mV vs. Ag/AgCl

Likelihood of a breakdown event scales with current magnitude

Drive single breakdown events – characterize the event signature – correlate events with evolved surface structure